
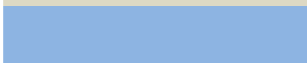
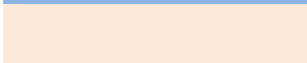



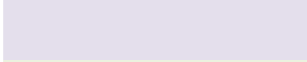
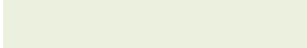



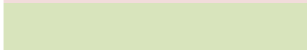


Tuesday, September 11											
9:00-12:20 Plenary Session (Yasuda Auditorium)											
Lunch											
School of Engineering Bldg.2 North Wing 1F Room 211	School of Engineering Bldg.2 North Wing 1F Room 212	School of Engineering Bldg.2 North Wing 1F Room 213	School of Engineering Bldg.2 North Wing 2F Room 221	School of Engineering Bldg.2 North Wing 2F Room 222	School of Engineering Bldg.2 North Wing 2F Room 223	School of Engineering Bldg.2 North Wing 3F Room 231	School of Engineering Bldg.2 Old Wing 3F Room 233	School of Engineering Bldg.2 North Wing 4F Room 241	School of Engineering Bldg.2 North Wing 4F Room 243	School of Engineering Bldg.2 North Wing 4F Room 244	School of Engineering Bldg.2 Old Wing 4F Room 246
14:00-15:15 A-1:Spin Transport	14:00-15:15 B-1:ReRAM	14:00-15:15 C-1:Nanowire and Nanostructure-Based FET	14:00-15:15 D-1:GaN Device Technologies I		14:00-15:15 F-1:High-Capacity-Anode Materials (Li, Si)	14:00-15:15 G-1:Interconnect-I	14:00-15:15 H-1:Germanium for Photonics Applications	14:00-15:15 J-1:Innovative Device Based Circuits I	14:00-15:15 K-1:Organic Light Emitting and Sensing Devices	14:00-15:15 M-1:Quantum Nano Photonics	14:00-15:15 N-1:Novel Thin Film Materials and Devices
Coffee Break											
15:30-17:15 A-2:Spintronics for AI and LSI Applications	15:30-16:30 B-2:Selector for Memory	15:30-16:30 C-2:Transistor Physics and Reliability	15:30-17:15 D-2:SiC MOS Interface		15:30-16:45 F-2:Battery / Fuel Cell		15:30-16:45 H-2:Si Photonic Integrated Circuits	15:30-17:15 J-2:Ion/Photon Coupled Systems	15:30-16:45 K-2:Organic Printing and Patterning Technologies	15:30-17:15 M-2:Optical Properties of 2D Materials	15:30-16:45 N-2:Crystal Growth of Group IV and Related Materials 1
Departure 19:20 / Arrival 21:20 Banquet Cruise											
Wednesday, September 12											
School of Engineering Bldg.2 North Wing 1F Room 211	School of Engineering Bldg.2 North Wing 1F Room 212	School of Engineering Bldg.2 North Wing 1F Room 213	School of Engineering Bldg.2 North Wing 2F Room 221	School of Engineering Bldg.2 North Wing 2F Room 222	School of Engineering Bldg.2 North Wing 2F Room 223	School of Engineering Bldg.2 North Wing 3F Room 231	School of Engineering Bldg.2 North Wing 3F Room 233	School of Engineering Bldg.2 North Wing 4F Room 241	School of Engineering Bldg.2 North Wing 4F Room 243	School of Engineering Bldg.2 North Wing 4F Room 244	School of Engineering Bldg.2 Old Wing 4F Room 246
9:00-10:30 A-3:Quantum Phenomena	9:00-10:30 B-3:In-Memory Computing I	9:00-10:30 C-3:Characterization and Process Technology	9:00-10:30 D-3:Ultrawide-Bandgap Semiconductor Devices I	9:00-10:30 E-3:Characterizations of Gate Dielectrics	9:15-10:30 F-3:Perovskite	9:00-10:15 G-3:3D Intergration	9:00-10:30 H-3:Heterogeneous Photonic Integrated Circuits on Si	9:00-10:30 J-3:Innovative Device Based Circuits II	9:00-10:30 K-3:Bio and Micro Systems	9:00-10:30 M-3:2D Materials & Devices I	9:00-10:30 N-3:Oxide Materials and Advanced Devices
Coffee Break											
10:45-12:00 A-4:Electrical Control of Magnetism	10:45-12:00 B-4:In-Memory Computing II	10:45-12:00 C-4:Ferroelectric and Tunnel FET I	10:45-12:00 D-4:Ultrawide-Bandgap Semiconductor Devices II	10:45-12:00 E-4:Advanced Materials Synthesis and Simulation	10:45-12:00 F-4:Perovskite	10:45-12:00 G-4:Advanced Bonding	10:45-12:00 H-4:Integration Technology for Photonic Applications	10:45-12:00 J-4:Thin Film Oxide Materials Based Devices and Systems	10:45-11:45 K-4:Organic Memory, Actuator and Sensing Devices	10:45-12:00 M-4:Nanowire Growth & Characterization	
Lunch											
Luncheon Seminar: Tektronix											
13:30-15:00 A-5:Novel Functional Devices	13:30-15:00 B-5:Gate Stack and Interface Engineering	13:30-15:00 Area1 & 2 C-5:Ferroelectric Hafnium Oxide: Breakthrough in Transistor and Memory I	13:30-15:00 D-5:High Frequency Devices/Narrow Gap Devices	13:30-15:00 E-5:Nanostructures: Synthesis and Properties	13:30-15:00 F-5:Si and Compounds		13:45-15:00 H-5:Photonic Devices and Platforms for Novel Applications	13:30-15:00 Area7 & Special J-5:Biomedical Devices and Systems	13:30-14:45 K-5:Organic Transistors	13:30-15:00 M-5:Physics & Application of Graphene Devices	13:30-14:30 N-5:Poly-Si TFT Technologies and Circuit Applications
Coffee Break											
15:15-16:30 A-6:New Materials and Physics in Spintronics	15:15-16:30 B-6:Process Technology	15:15-16:30 Area1 & 2 C-6:Ferroelectric Hafnium Oxide: Breakthrough in Transistor and Memory II	15:15-16:30 D-6:Silicon Devices and Processes	15:15-16:30 E-6:Group IV Materials	15:15-16:30 F-6:Quantum Dot	15:15-16:15 G-6:Interconnect-II	15:15-16:15 H-6:Hybrid Devices and Materials	15:15-17:00 J-6:Advanced Image Sensors	15:15-16:30 K-6:Biodevices and Materials	15:15-16:30 M-6:Nano-Structure Devices	15:15-16:30 N-6:New Functional Materials and Devices
16:30-17:15 Short Presentation Area9	16:30-17:15 Short Presentation Area2	16:30-17:15 Short Presentation Area1	16:30-17:15 Short Presentation Area4		16:30-17:15 Short Presentation Area6			17:00-17:15 Short Presentation Special	16:30-17:15 Short Presentation Area7	16:30-17:15 Short Presentation Area8	16:30-17:15 Short Presentation Area10
	Short Presentation Area3		Short Presentation Area11							Short Presentation Area5	
17:30-19:00 Rump Sessions (Faculty of Engineering Bldg.2 Room 213)											
Thursday, September 13											
School of Engineering Bldg.2 North Wing 1F Room 211	School of Engineering Bldg.2 North Wing 1F Room 212	School of Engineering Bldg.2 North Wing 1F Room 213	School of Engineering Bldg.2 North Wing 2F Room 221	School of Engineering Bldg.2 North Wing 2F Room 222	School of Engineering Bldg.2 North Wing 2F Room 223	School of Engineering Bldg.2 North Wing 3F Room 231	School of Engineering Bldg.2 North Wing 3F Room 233	School of Engineering Bldg.2 North Wing 4F Room 241	School of Engineering Bldg.2 North Wing 4F Room 243	School of Engineering Bldg.2 North Wing 4F Room 244	School of Engineering Bldg.2 North Wing 4F Room 246
9:00-10:45 A-7:Quantum Computational Devices	9:00-10:45 B-7:Flash and 1T-DRAM	9:00-10:45 C-7:Ferroelectric and Tunnel FET II	9:00-10:45 D-7:GaN Device Technologies II	9:00-10:45 E-7:Advanced Growth of Widegap Semiconductors	9:45-10:45 F-7:Photocatalyst/Solar Cells	9:00-10:45 G-7:MEMS Application		9:00-10:45 Area5 & Special J-7:LiDAR and Imaging Applications	9:00-11:00 K-7:Chemical and Gas Sensors	9:00-10:45 M-7:2D Materials & Devices II	9:00-10:15 N-7:Advanced IGZO Processes and Devices
Coffee Break											
11:00-13:30 Poster Session (Ito International Research Center, Ito Hall)											
Lunch											
14:00-16:00 A-8:Spin-Orbit Interaction		14:00-15:45 C-8:Group III-V and Ge Technology	14:00-15:45 D-8:SiC Devices and Processes		14:00-15:45 Area6 & 11 F-8:Thermoelectric Materials		14:00-15:30 H-8:Light Emitting Devices and Photodiodes	14:00-16:00 Area1 & Special J-8:Innovative Device Based Circuits III	14:00-15:30 K-8:Molecular Materials and Devices		14:00-15:15 N-8:Crystal Growth of Group IV and Related Materials 2

Area Scope		Area 1: Advanced CMOS: Material Fundamentals, Process Science and Device Physics
		Area 2: Advanced / Emerging Memories and New Applications
		Area 3: Interconnection / 3D Integrations / MEMS
		Area 4: Power / High-speed Devices, and Materials
		Area 5: Advanced Photonics: Devices, Integration and Related Technology
		Area 6: Photovoltaic / Energy Harvesting / Battery-related Technology
		Area 7: Organic / Molecular / Bio-electronics
		Area 8: Low Dimensional Devices and Materials

Area Scope		Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
		Area 10: Thin Film Electronics: Oxide, Non-single Crystalline and Novel Process
		Area 11: Advanced Materials Synthesis and Advanced Characterization
		Special: Advanced Circuits/Systems Interacting with Innovative Devices & Materials